

Title (en)

A SEMICONDUCTOR CRYSTAL GROWTH APPARATUS

Publication

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Application

EP 88303510 A 19880419

Priority

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- JP 10369987 A 19870427

Abstract (en)

[origin: EP0288242A1] A semiconductor crystal growth apparatus comprises a preparation chamber (401) for inserting a substrate into and out of the apparatus, a cleaning chamber (403) for cleaning a surface of the substrate and a growth chamber (406) for forming an epitaxial layer on the cleaned substrate.

IPC 1-7

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IPC 8 full level

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CPC (source: EP US)

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Citation (examination)

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